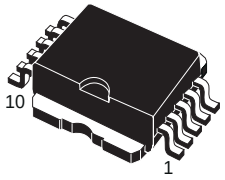
VN710SP

AUTOMOTIVE GLOW PLUG DRIVER

PRELIMINARY DATA

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VN710SP	18mΩ	35 A	16 V

- CMOS COMPATIBLE INPUT
- ON STATE OPEN LOAD DETECTION
- OFF STATE OPENLOAD DETECTION
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- PROTECTION AGAINST LOSS OF GROUND
- VERY LOW STAND-BY CURRENT WHEN ENABLE PIN IS LOW
- REVERSE BATTERY PROTECTION (*)

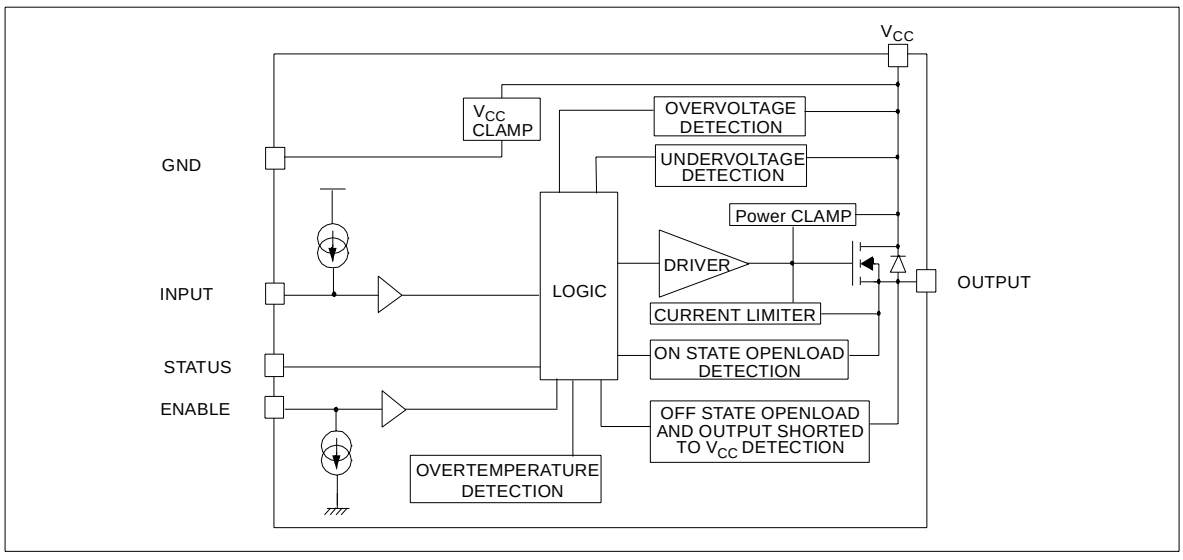


PowerSO-10™

DESCRIPTION

The VN710SP is a monolithic device made using STMicroelectronics VIPower M0-3 technology, intended for driving any kind of load with one side connected to ground. Active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transients compatibility table). Active current limitation combined with thermal shutdown protect the device against overload. After a thermal shutdown event, device stays latched off and diagnostic stays at a low level until next falling edge of input signal. The device detects open load condition both in on state and off state. Output shorted to V_{CC} is detected in the off state. Device automatically turns off in case of ground pin disconnection. Enable pin allows to switch the device to idle state with very low quiescent current from V_{CC}. When enable is low, device turns off regardless of input pin state.

BLOCK DIAGRAM



(*) See application schematic at page 7

THERMAL DATA

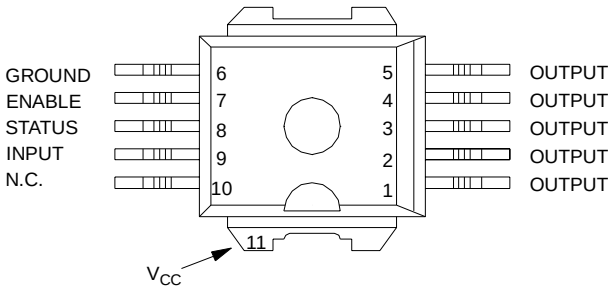
Symbol	Parameter	Value	Unit
$R_{tj\text{-}case}$	Thermal resistance junction-case	1.4	°C/W
$R_{tj\text{-}amb}$ (*)	Thermal resistance junction-ambient	52	°C/W

(*) When mounted on a standard single-sided FR-4 board with 50mm^2 of Cu (at least 35µm thick).

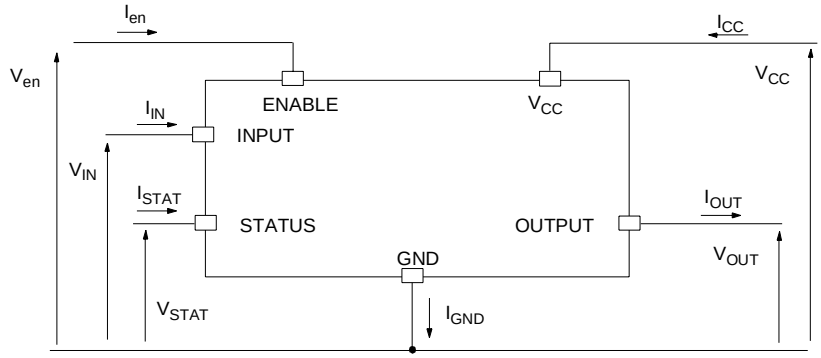
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	41	V
$-V_{CC}$	Reverse DC supply voltage	-0.3	V
$-I_{GND}$	Reverse DC ground pin current	-200	mA
I_{OUT}	DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	-35	A
I_{IN}	DC input current	+/-10	mA
I_{en}	DC enable current	+/-10	mA
I_{STAT}	DC status current	+/-10	mA
V_{ESD}	Electrostatic discharge (R=1.5kΩ; C=100pF)	2000	V
P_{tot}	Power dissipation at T_c=25°C	89	W
T_j	Junction operating temperature	Internally limited	°C
T_c	Case operating temperature	-40 to 150	°C
T_{stg}	Storage temperature	-55 to 150	°C

CONNECTION DIAGRAM (TOP VIEW)



CURRENT AND VOLTAGE CONVENTIONS



ELECTRICAL CHARACTERISTICS (7V<V_{CC}<16V; -40°C<T_j<150°C; unless otherwise specified)

POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{CC}	Operating supply voltage		5.5	13	16	V
V_{USD}	Undervoltage shutdown		3	4	5.5	V
V_{OV}	Overvoltage shutdown		16	18	20	V
R_{ON}	On state resistance	I_{OUT}=15A; T_j=25°C I_{OUT}=15A			20 40	mΩ mΩ
I_S	Supply current	Off state; V_{CC}=13V; V_{en}=V_{OUT}=0V; V_{IN}=5V Off state; V_{CC}=13V; V_{en}=V_{OUT}=0V; V_{IN}=5V; T_j=25°C On state; V_{CC}=13V; V_{IN}=0V; I_{OUT}=0A; V_{en}>V_{enh}		10 10 2.5	25 20 4	µA µA mA
I_{LGND}	Output current at Turn-off	V_{CC}=V_{GND}=16V V_{IN}=V_{en}=n.c.; V_{OUT}=0V			2	mA
$I_{L(off1)}$	Off state output current	V_{OUT}=0V; V_{IN}>V_{IH}	0		50	µA
$I_{L(off2)}$	Off state output current	V_{OUT}=3.5V; V_{IN}>V_{IH}; V_{en}>V_{enh}	-75		0	µA

SWITCHING (V_{CC}=13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on delay time	R_L=0.85Ω, from V_{IN} falling edge to V_{OUT}=1.3V		40		µs
$t_{d(off)}$	Turn-off delay time	R_L=0.85Ω, from V_{IN} rising edge to V_{OUT}=11.7V		80		µs
$dV_{OUT}/dt_{(on)}$	Turn-on voltage slope	R_L=0.85Ω, from V_{OUT}=1.3V to V_{OUT}=10.4V		0.1		V/µs
$dV_{OUT}/dt_{(off)}$	Turn-off voltage slope	R_L=0.85Ω, from V_{OUT}=11.7V to V_{OUT}=1.3V		0.1		V/µs

INPUT PIN (active low)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level				1.25	V
I_{IL}	Low level input current	V_{IN}=1.25V; V_{en}>V_{enh}	-35			µA
V_{IH}	Input high level		3.25			V
I_{IH}	High level input current	V_{IN}=3.25V; V_{en}>V_{enh} V_{IN}=3.25V; V_{en}=0V	 -300		-4 -4	µA µA
$V_{I(hyst)}$	Input hysteresis voltage		0.5			V
V_{ICL}	Input clamp voltage	I_{IN}=1mA I_{IN}=-1mA	6	6.8 -0.7	8	V V

ENABLE PIN (active high)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{enl}	Enable low level				1.25	V
I_{enl}	Low level enable current	V_{en}=1.25V	4			µA
V_{enh}	Enable high level		3.25			V
I_{enh}	High level enable current	V_{en}=3.25V			35	µA
V_{ehyst}	Enable hysteresis voltage		0.5			V
V_{encl}	Enable clamp voltage	I_{en}=1mA I_{en}=-1mA	6	6.8 -0.7	8	V V

ELECTRICAL CHARACTERISTICS (continued)

STATUS PIN (Open Drain)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{STAT}	Status low output voltage	I_{STAT}=1.6mA			0.5	V
I_{LSTAT}	Status leakage current	Normal operation; V_{STAT}=5V			10	µA
C_{STAT}	Status pin input capacitance	Normal operation; V_{STAT}=5V			100	pF
V_{SCL}	Status clamp voltage	I_{STAT}=1mA I_{STAT}=-1mA	6	6.8 -0.7	8	V V

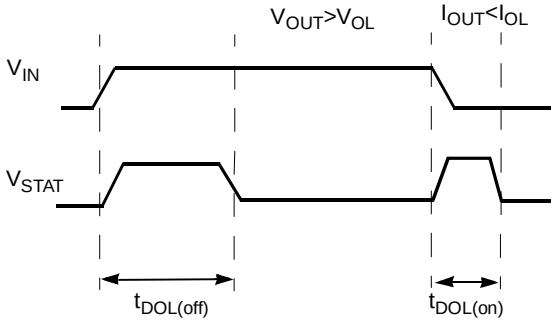
PROTECTIONS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T_{TSD}	Shut-down temperature		170	190		°C
T_R	Reset temperature		135			°C
T_{hyst}	Thermal hysteresis		7	15		°C
t_{SDL}	Overload detection delay	T_j>T_{TSD}			20	µs
I_{lim}	Current limitation		35	55	80	A
V_{demag}	Turn-off output clamp voltage	I_{OUT}=2A; V_{IN}=5V; L=6mH	V_{CC}-41	V_{CC}-48	V_{CC}-55	V

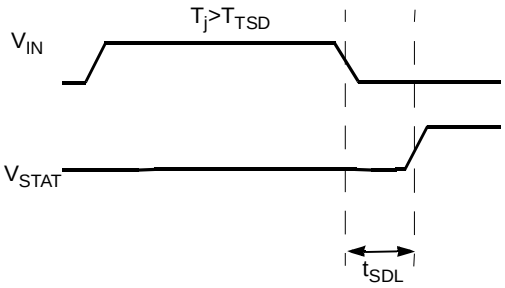
OPENLOAD DETECTION

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_{OL}	Openload on state detection threshold	V_{IN}=0V	0.1	1	2	A
V_{OL}	Openload off state voltage detection threshold	V_{IN}=5V	1.5	2.5	3.5	V
$t_{DOL(off)}$	Openload detection delay at turn-off				500	µs
$t_{DOL(on)}$	Openload detection delay at turn-on	I_{OUT}=0V			200	µs

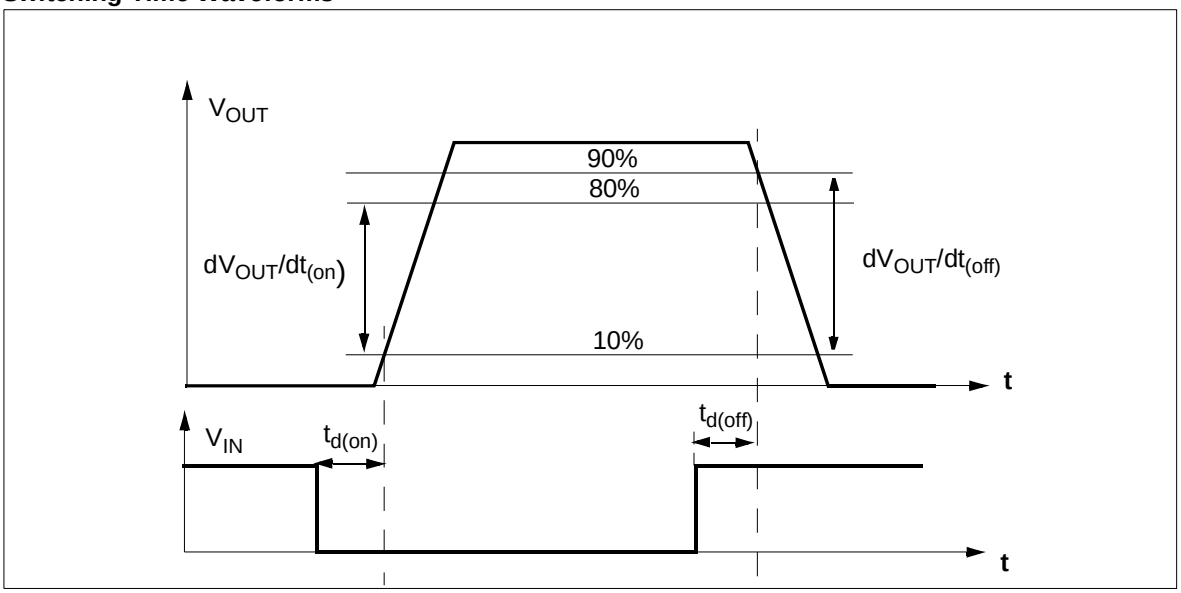
OPENLOAD STATUS TIMING (with external pull-up)



OVERTEMP STATUS TIMING



Switching Time Waveforms



TRUTH TABLE

CONDITIONS	ENABLE	INPUT	OUTPUT	STATUS
Normal operation	H H	H L	L H	H H
Current limitation	H H	H L	L X	H H
Overtemperature	H H	L H	L (*) L	L (*) L
Undervoltage	H H	H L	L L	X X
Overvoltage	H H	H L	L L	H H
Output voltage > V_{OL}	H H	H L	H H	L H
Output current < I_{OL}	H H	H L	L H	H L
Any	L	X	L	H

(*) Latched on first overtemperature event; latch cleared on next input falling edge.

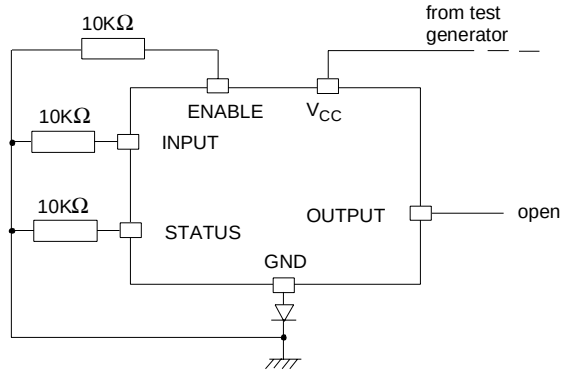
ELECTRICAL TRANSIENTS REQUIREMENTS ON V_{CC} PIN

ISO T/R 7637/1 Test Pulse	TEST LEVELS				
	I	II	III	IV	Delays and Impedance
1	-25V	-50V	-75V	-100V	2ms, 10Ω
2	+25V	+50V	+75V	+100V	0.2ms, 10Ω
3a	-25V	-50V	-100V	-150V	0.1ms, 50Ω
3b	+25V	+50V	+75V	+100V	0.1ms, 50Ω
4	-4V	-5V	-6V	-7V	100ms, 0.01Ω
5	+26.5V	+46.5V	+66.5V	+86.5V	400ms, 2Ω

ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULT			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

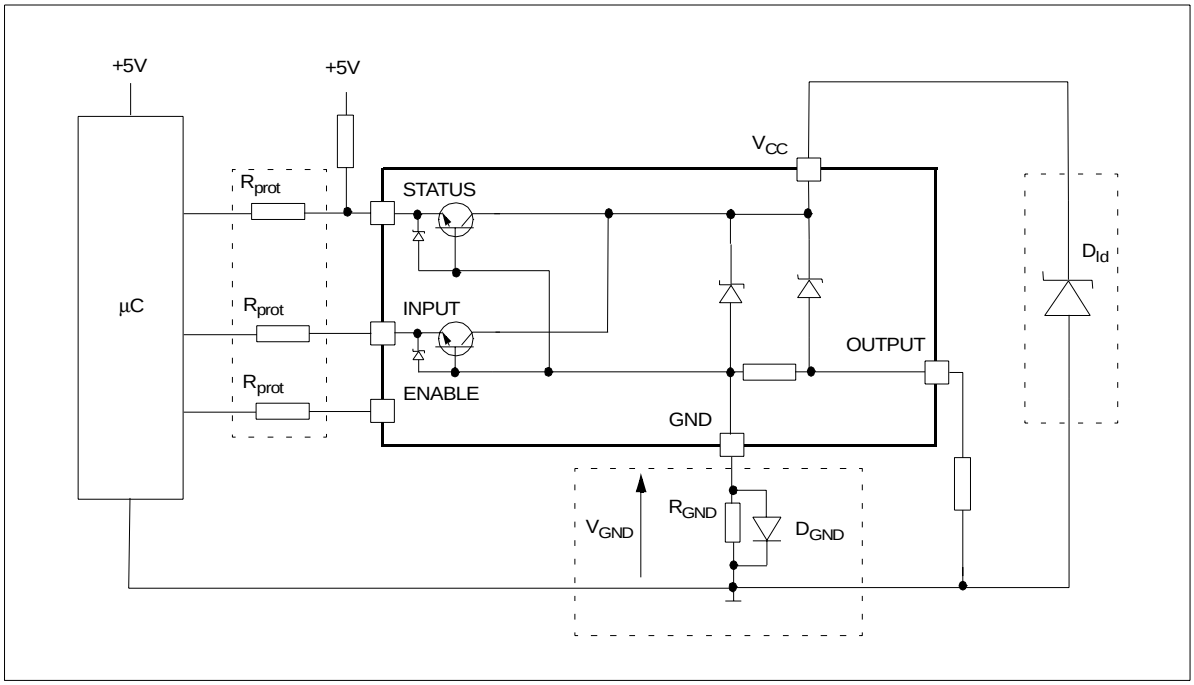
CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

SUGGESTED SCHEME FOR ISO TEST PULSE



Warning: Input, Enable, Status Pulled to V_{CC} voltage during negative transient.

APPLICATION SCHEMATIC



GND PROTECTION NETWORK AGAINST REVERSE BATTERY

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

1) $R_{GND} \leq 600mV / (I_{S(on)max})$.

2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the of the device's datasheet.

Power Dissipation in R_{GND} (when V_{CC}<0: during reverse battery situations) is:

$P_D= (-V_{CC})^2/R_{GND}$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on many devices are ON in the case of several high side drivers sharing the same R_{GND}.

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggest to utilize Solution 2 (see below).

Solution 2: A diode (D_{GND}) in the ground line.

A resistor (R_{GND}=1kΩ) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift (≃600mV) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

LOAD DUMP PROTECTION

D_{ld} is necessary (Transil or MOV) if the load dump peak voltage exceeds V_{CC} max DC rating. The same applies if the device will be subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

µC I/Os PROTECTION:

If a ground protection network is used and negative transient are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the µC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of µC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of µC I/Os.

$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C}-V_{IH}-V_{GND}) / I_{IHmax}$

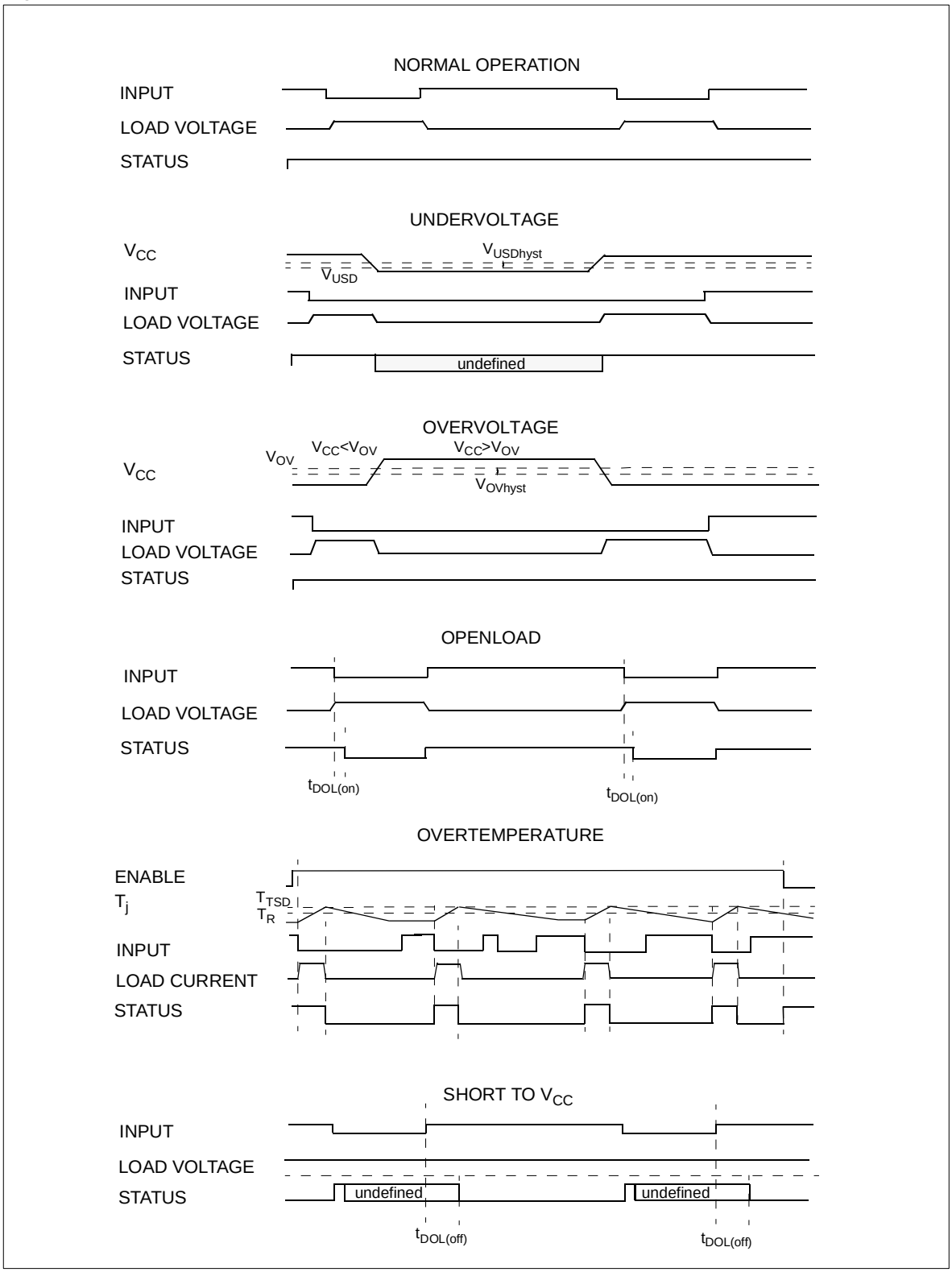
Calculation example:

For V_{CCpeak}= - 100V and $I_{latchup} \geq$ 20mA; $V_{OH\mu C} \geq$ 4.5V

5kΩ ≤ R_{prot} ≤ 18.57kΩ.

Recommended R_{prot} value is10kΩ.

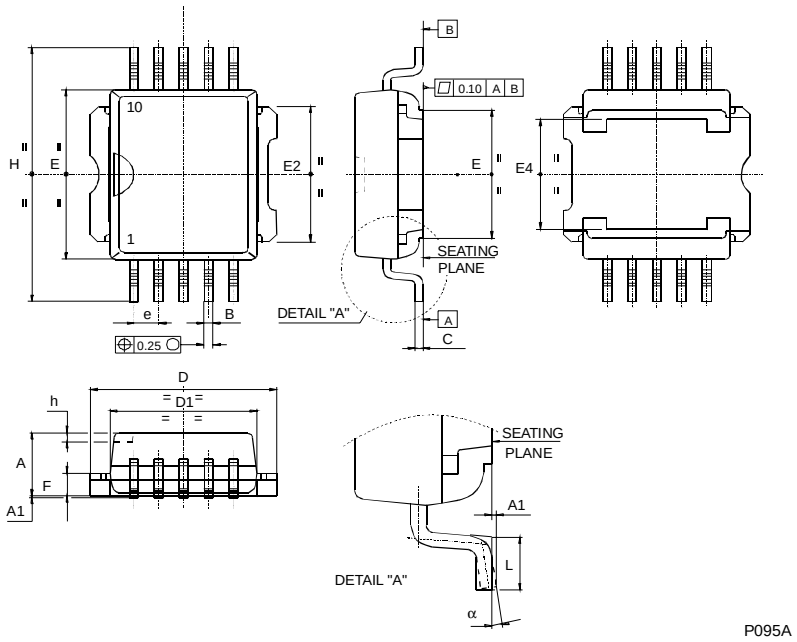
Figure1: Waveforms



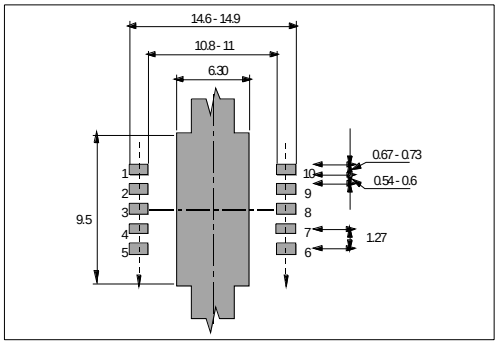
PowerSO-10™ MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	3.35		3.65	0.132		0.144
A (*)	3.4		3.6	0.134		0.142
A1	0.00		0.10	0.000		0.004
B	0.40		0.60	0.016		0.024
B (*)	0.37		0.53	0.014		0.021
C	0.35		0.55	0.013		0.022
C (*)	0.23		0.32	0.009		0.0126
D	9.40		9.60	0.370		0.378
D1	7.40		7.60	0.291		0.300
E	9.30		9.50	0.366		0.374
E2	7.20		7.60	0.283		300
E2 (*)	7.30		7.50	0.287		0.295
E4	5.90		6.10	0.232		0.240
E4 (*)	5.90		6.30	0.232		0.248
e		1.27			0.050	
F	1.25		1.35	0.049		0.053
F (*)	1.20		1.40	0.047		0.055
H	13.80		14.40	0.543		0.567
H (*)	13.85		14.35	0.545		0.565
h		0.50			0.002	
L	1.20		1.80	0.047		0.070
L (*)	0.80		1.10	0.031		0.043
α	0º		8º	0º		8º
α (*)	2º		8º	2º		8º

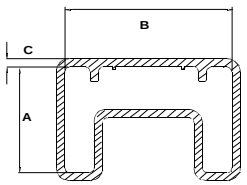
(*) Muar only POA P013P



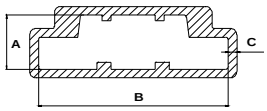
PowerSO-10™ SUGGESTED PAD LAYOUT



TUBE SHIPMENT (no suffix)



CASABLANCA

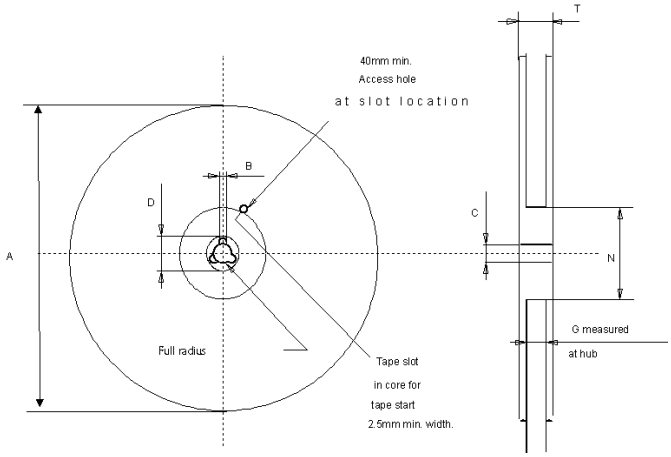


MUAR

All dimensions are in mm.

	Base Q.ty	Bulk Q.ty	Tube length (± 0.5)	A	B	C (± 0.1)
Casablanca	50	1000	532	10.4	16.4	0.8
Muar	50	1000	532	4.9	17.2	0.8

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

Base Q.ty	600
Bulk Q.ty	600
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+ 2 / -0)	24.4
N (min)	60
T (max)	30.4

All dimensions are in mm.

TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	**W**	24
Tape Hole Spacing	**P0 (± 0.1)**	4
Component Spacing	**P**	24
Hole Diameter	**D (± 0.1/-0)**	1.5
Hole Diameter	**D1 (min)**	1.5
Hole Position	**F (± 0.05)**	11.5
Compartment Depth	**K (max)**	6.5
Hole Spacing	**P1 (± 0.1)**	2

All dimensions are in mm.